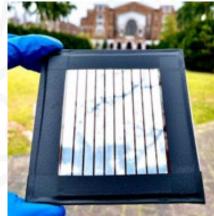
University at Buffalo The State University of New York

MAPbBr_{3-x}Cl_x



Dependence of the solar cells and the interfaces

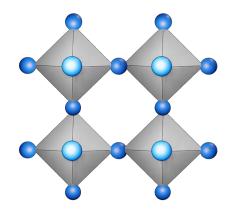
Wanyi Nie Associate Professor, Department of Physics SUNY University at Buffalo wanyinie@buffalo.edu



Tandem solar cell

Perovskite for high efficiency photovoltaics

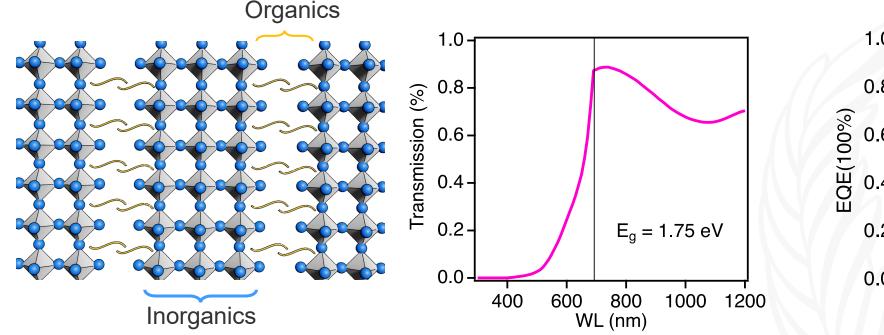
3D perovskite ABX₃

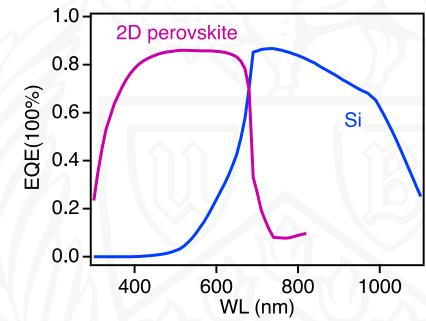


A = Cations B = Pb, Sn X = halides Solution grown semiconductor for ultra-thin solar cell

- Single junction perovskite cell with 25% power conversion efficiencies demonstrated
- Wide gap perovskite top cell can boost Si cell's efficiency to approach 40% by building a tandem
- Radiation hardness properties feasible for space PV
- However, wide gap 3D perovskite isn't stable

2D perovskite solar cell is an intrinsically stable top cell material for tandem





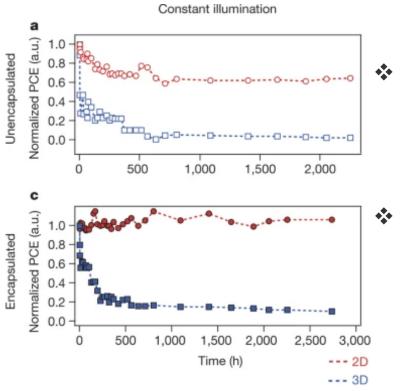
 2D perovskite has an intrinsic band gap of 1.75 eV by the quantum confinement effect

Ahn et al, under prep (2024)

 Our optical simulation shows an ideal band gap matching with low band gap Si cell

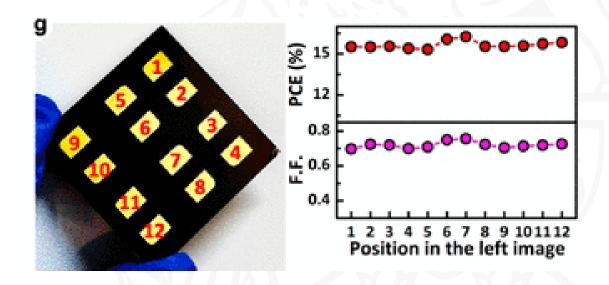
Stability and upscaling

Better stability of 2D perovskite



- PCE of 12.5%
 obtained from a
 2D perovskite
 solar cell
- 2D cell shows a much stable performance under constant illumination
- Tsai-Nie et al, Nature, 536, 312 (2016); Tsai et al., Adv. Mater., 30, 1704217(2018)

 Upscaling method for 2D perovskite solar module

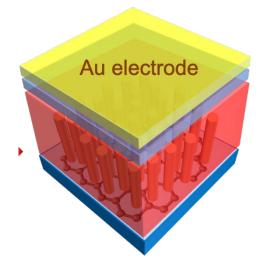


PCE > 15% achieved from a 2D large area device

> Huang et al, ACS Materials Lett. 2023, 5, 5, 1384–1394

GaN as robust n-type interface

GaN is a n-type, rad-hard semiconductor



We built a PIN diode with perovskite/GaN interface GaN Derovskite

(2.4)(2.4)(2.4)(2.4)(1.6

Stable current output under 200 cycles of X-ray

irradiation in ambient air

Kim et al, submitted (2024)